H<sup>-</sup> formation by scattering of hydrogen atoms/ions on carbonaceous surfaces

### H. Khemliche, N. Bundaleski, V. Esaulov, P. Roncin

Laboratoire des collisions atomiques et moléculaires Université Paris-Sud 11, Orsay, France



Bouillabaisse

## Fundamental processes: metals v.s. insulators





## Experimental approach: grazing incidence



#### Limited number of inelastic processes $\Rightarrow$ access to individual basic processes

## Fundamental processes: metals v.s. insulators



H. Winter, Progress in Surface Science **63**, 177, 2000 A.G. Borisov, V. Sidis

Negative ion formation from neutrals:

- threshold in parallel velocity (kinematic effect)
- competition between capture and electron loss

Incident atoms with low energy  $\Rightarrow$  very low yield of negative ions... ...unless surface has a low work-function (Cs)

## Fundamental processes: simultaneous double capture





At low energy, it is easier to capture two electrons rather than one !!!

Systemes where double capture has been obeserved:

- $F^+$  on LiF(001)  $\Rightarrow F^-$  fraction ~ 40 %
- $O^+$  on NaCl(001)  $\Rightarrow O^-$  fraction ~ 7 %
- $H^+$  on NaCl(001)  $\Rightarrow H^-$  fraction ~ 1 %

# **Results from diamond**

CVD grown diamond, naturally hydrogenated

- band gap  $\sim 5.5~eV$
- very deep valence band
- negative electron affinity (-1 eV), depending on H surface coverage

 $\Rightarrow$  Virtually very good candidate for negative ion formation & survival

	СВ	
5-	gap	H <sup>-</sup> (0.75eV)
10		
15	VB	H° (13 6eV)
20		(15.00 V)

Projectile E=1 keV	Fraction of H <sup>-</sup> (%)
$\mathrm{H}^+$	$2.5 \pm 0.5$
H°	$3.0 \pm 0.8$
$H_{2}^{+}$	$1.6 \pm 0.5$

**Résults with H<sub>2</sub><sup>+</sup> in agreement with literature** (Wurz P., Schletti R. and Aellig M.R., Surf. Sci **373**, 56, 1997)

<u>Conclusion</u>: CVD diamond behaves like a common ionic insulator (LiF, NaCl)

 $\Rightarrow$  survival of transient H<sup>-</sup> favored by band gap

## Results from graphite, first glance...

#### Graphite HOPG

- semi-metal (conductor)
- work-function  $\sim 5 \text{ eV}$
- deep valence band



CB

5

10

H<sup>-</sup>(0.75eV)

### Results from graphite, more...



- H<sup>-</sup> fractions barely depend on incident charge state (efficient neutralizaton of H<sup>+</sup>)
- variation with E<sub>total</sub> (competition capture/loss) is comparable to that observed on LiF(001) !
- H<sup>-</sup> fractions increase with  $E_{\perp}$  $\Rightarrow$  is there a maximum in En?

Results from graphite, more...

These results are characteristic of a clean graphite:

- H- fraction increases after annealing to 600°C (no contamination)
- low defect concentration





### $\Rightarrow$ Influence of contamination and defects (plasma conditions) on H<sup>-</sup> production ?

## Conclusions

### <u>Diamand:</u>

- results below expectations (not better than LiF)
  - $\rightarrow$  question over actual H surface coverage
  - $\rightarrow$  question over surface quality

## <u>Graphite:</u>

- -H- fractions unexpected and promising (capture from H°)
- possible to get more than 10% H<sup>-</sup> for normal energies > 5 eV
- $\rightarrow$  Formation mechanism not clear
- $\rightarrow$  HOPG is either a metal (energy loss) or an insulator (H- yield, e- emission)



Energy loss spectrum

## Perspectives

#### It seems that carboneceous materials offer good surprises

- -Extend our work on graphite and possibly on hydrogenated diamond
  - $\rightarrow$  exploit energy loss data in coincidence with electron emission
  - ightarrow go to larger incidence angles (avoid detachment)
  - $\rightarrow$  investigate graphite with H and/or defects
- investigate other carbon based materials ( $C_{60}$ ...)

Best candidate material (in theory):

